

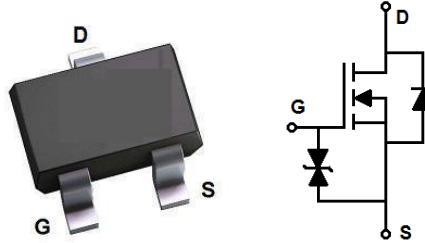


$V_{(BR)DSS}$	$R_{DS(on)} \text{ Typ}$	$I_D \text{ Max}$
60V	1.9Ω @ 10V	0.3A
	2.1Ω @ 4.5V	

## Features

- Low  $R_{DS(on)}$  @  $V_{GS}=10V$
- 5V Logic Level Control
- N Channel SOT323 Package
- ESD Protection
- Pb-Free, RoHS Compliant

SOT323



## Applications

- Logic level translators
- High-speed line drivers
- Low-side load switch
- Switching circuits
- Relay driv

## Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit	
<b>Common Ratings (<math>T_A=25^\circ\text{C}</math> Unless Otherwise Noted)</b>				
$V_{GS}$	Gate-Source Voltage	±20	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	60	V	
$T_J$	Maximum Junction Temperature	150	°C	
$T_{STG}$	Storage Temperature Range	-50 to 150	°C	
Mounted on Large Heat Sink				
$I_{DM}$	Pulse Drain Current Tested①	$T_A=25^\circ\text{C}$	1.2	A
$I_D$	Continuous Drain Current( $V_{GS}=4.5V$ )	$T_A=25^\circ\text{C}$	0.3	A
		$T_A=70^\circ\text{C}$	0.24	
$P_D$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	0.3	W
		$T_A=70^\circ\text{C}$	0.2	
$R_{JA}$	Thermal Resistance Junction-Ambient	400	°C/W	



**2N7002KW**  
60V/0.3A N Channel Advanced Power MOSFET



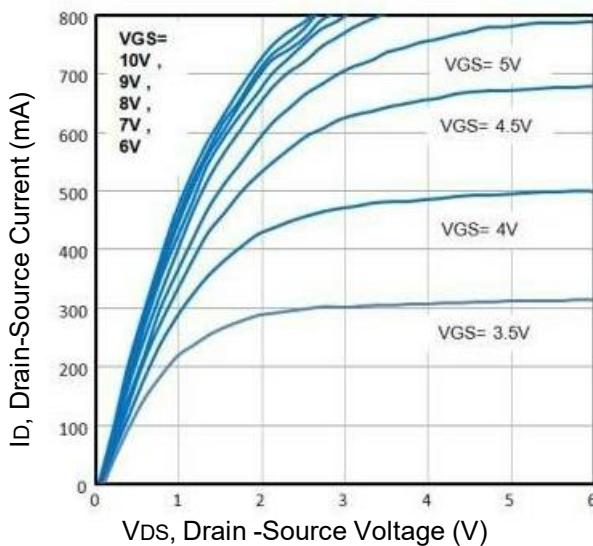
Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	60	-	-	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current( $T_A=25^\circ\text{C}$ )	$V_{\text{DS}}=60\text{V}$ , $V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
	Zero Gate Voltage Drain Current( $T_A=125^\circ\text{C}$ )	$V_{\text{DS}}=48\text{V}$ , $V_{\text{GS}}=0\text{V}$	-	-	100	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	-	-	$\pm 10$	$\mu\text{A}$
$V_{\text{GS}(\text{TH})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$ , $I_D=250\mu\text{A}$	1.0	1.9	2.5	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=10\text{V}$ , $I_D=0.3\text{A}$	-	1.9	3	$\Omega$
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=4.5\text{V}$ , $I_D=0.3\text{A}$	-	2.1	4	$\Omega$
<b>Dynamic Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=30\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	-	16	-	pF
$C_{\text{oss}}$	Output Capacitance		-	3.8	-	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		-	0.6	-	pF
$Q_g$	Total Gate Charge	$V_{\text{DS}}=30\text{V}$ , $I_D=0.5\text{A}$ , $V_{\text{GS}}=10\text{V}$	-	0.72	-	nC
$Q_{\text{gs}}$	Gate Source Charge		-	0.15	-	nC
$Q_{\text{gd}}$	Gate Drain Charge		-	0.22	-	nC
<b>Switching Characteristics</b>						
$t_{\text{d}(\text{on})}$	Turn on Delay Time	$V_{\text{DD}}=30\text{V}$ , $I_D=0.3\text{A}$ , $R_G=3.3\Omega$ , $V_{\text{GS}}=10\text{V}$	-	5	-	ns
$t_r$	Turn on Rise Time		-	3.3	-	ns
$t_{\text{d}(\text{off})}$	Turn Off Delay Time		-	18	-	ns
$t_f$	Turn Off Fall Time		-	5.2	-	ns
<b>Source Drain Diode Characteristics</b>						
$I_{\text{SD}}$	Source drain current(Body Diode)	$T_A=25^\circ\text{C}$	-	-	0.5	A
$V_{\text{SD}}$	Forward on voltage②	$T_j=25^\circ\text{C}$ , $I_{\text{SD}}=0.5\text{A}$ , $V_{\text{GS}}=0\text{V}$	-	0.73	1.2	V

#### Notes:

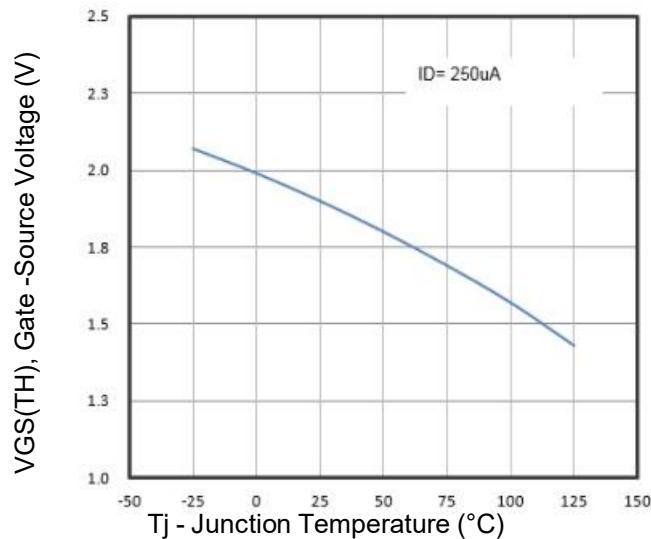
- ① Pulse width limited by maximum allowable junction temperature
- ②Pulse test ; Pulse width $\leq 300\mu\text{s}$ , duty cycle $\leq 2\%$ .



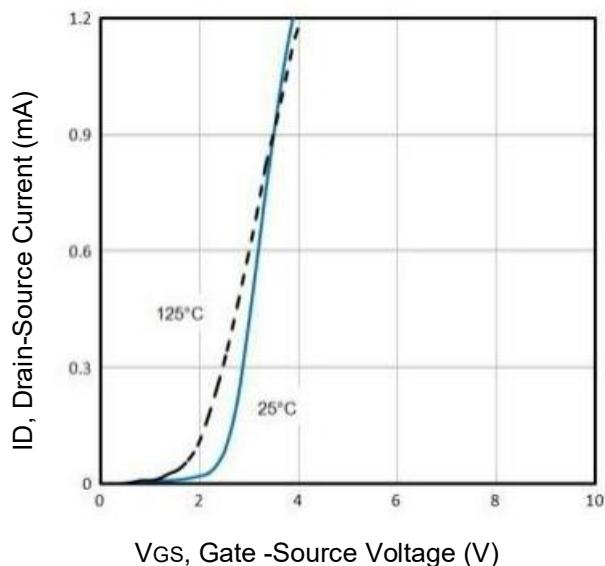
### Typical Characteristics



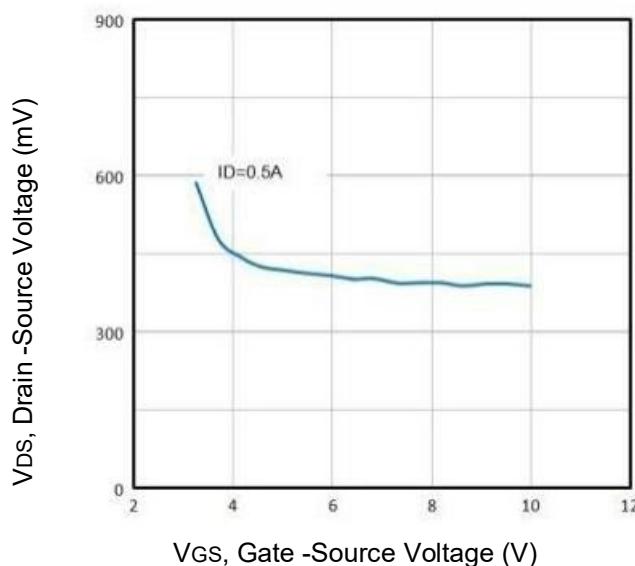
**Fig1.** Typical Output Characteristics



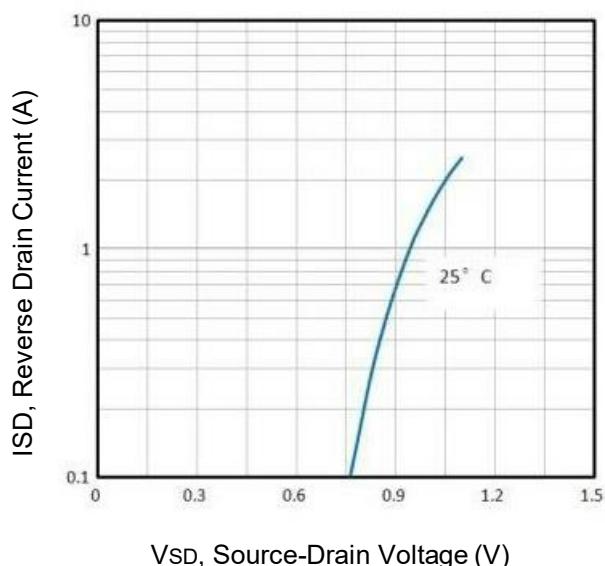
**Fig2.** Normalized Threshold Voltage Vs. Temperature



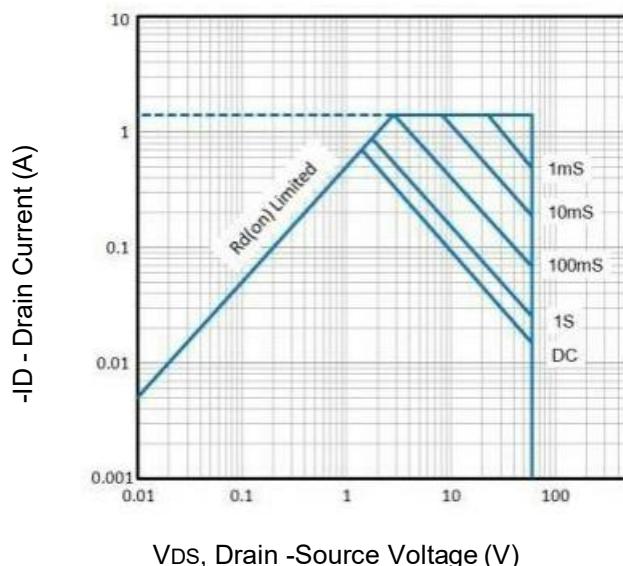
**Fig3.** Typical Transfer Characteristics



**Fig4.** Drain -Source Voltage vs Gate -Source Voltage



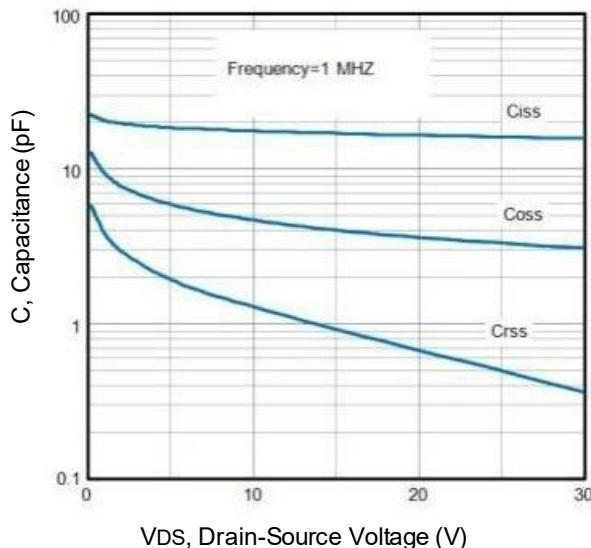
**Fig5.** Typical Source-Drain Diode Forward Voltage



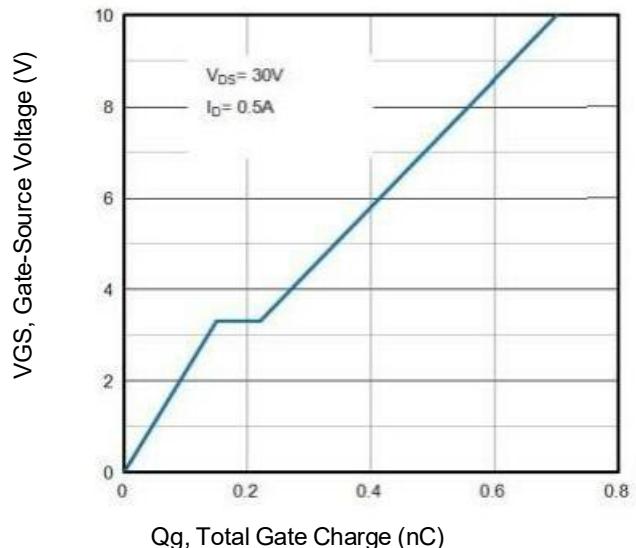
**Fig6.** Maximum Safe Operating Area



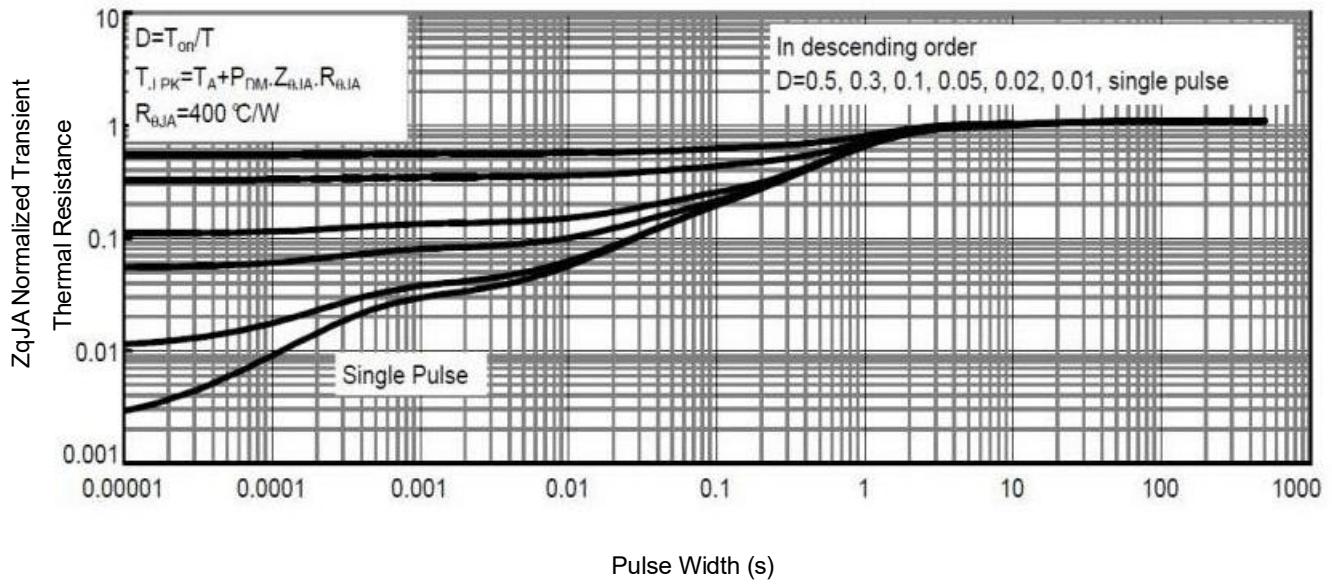
## Typical Characteristics



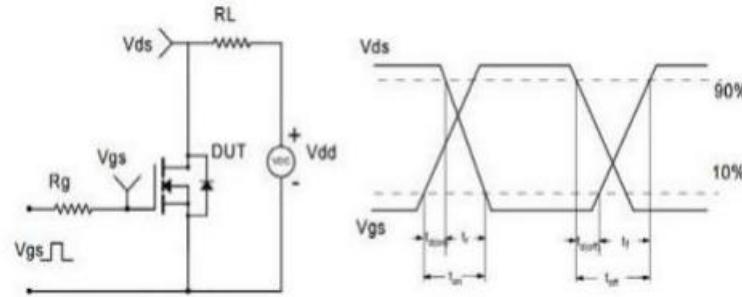
**Fig7.** Typical Capacitance Vs. Drain-Source Voltage



**Fig8.** Typical Gate Charge Vs. Gate-Source Voltage



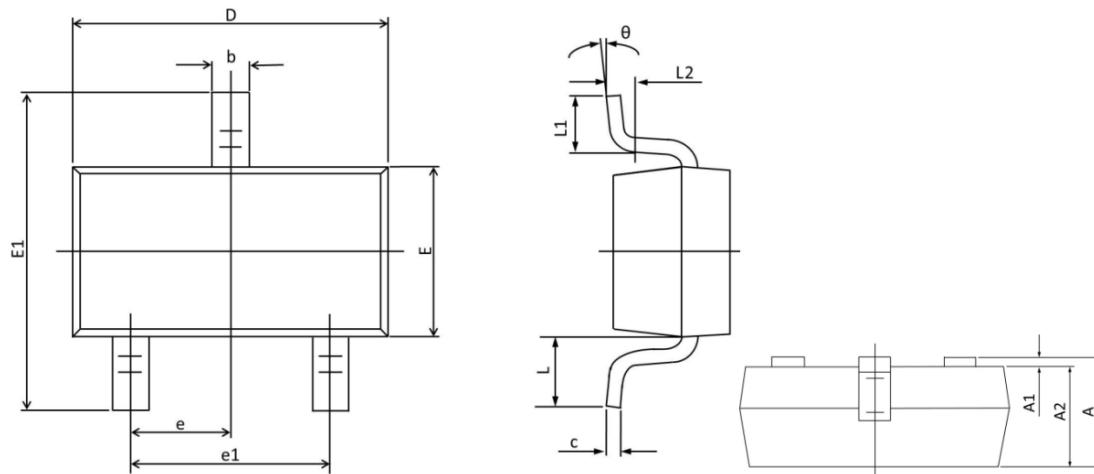
**Fig9.** Normalized Maximum Transient Thermal Impedance



**Fig10.** Switching Time Test Circuit and waveforms



### SOT-323 Mechanical Data



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
A1	0.100	0.000	0.004	0.000
A2	1.000	0.800	0.039	0.031
b	0.400	0.200	0.016	0.008
c	0.250	0.080	0.010	0.003
D	2.200	1.800	0.087	0.071
E	1.350	1.150	0.053	0.045
E1	2.450	1.800	0.096	0.071
e	0.65BSC		0.026BSC	
e1	1.400	1.200	0.055	0.047
L	0.525REF.		0.021REF.	
L1	0.460	0.150	0.018	0.006
L2	0.200	0.000	0.008	0.000
θ	8°	0°	8°	0°

### Ordering Information

Part No.	Marking	Package	Shipping Quantity
2N7002KW	7002	SOT-323	3000PCS/Reel